

## CLAIMS:

1. A method of preparing a precursor solution for a crystalline layer comprising an oxide of lead, niobium and a third metal, comprising the steps of:
  - providing a first solution of a lead salt that is chelated with a macrocyclic compound having a cavity corresponding to the size of the lead-ion, in a solvent chosen from the group of alkoxyalcohols;
  - providing a second solution comprising niobium in the form of alcoholates;
  - and
  - mixing the first and the second solution.
2. A method as claimed in claim 1, characterized in that the lead salt is chosen such that on mixing the first and the second solution at least one ester will be formed.
3. A method as claimed in claim 1, characterized in that the third metal is magnesium, which is present in the second solution.
4. A method as claimed in claim 2, characterized in that the lead salt is chosen from the group of carboxylates and nitrates.
5. A method as claimed in claim 1, characterized in that the macrocyclic compound is a 18-crown-6 ether.
6. A precursor solution for a crystalline layer comprising an oxide of lead, niobium and a third metal obtainable by the method of claims 1 to 5.
7. A method of manufacturing an electronic device comprising the step of applying a precursor solution for a crystalline layer comprising an oxide of lead, niobium and a third metal onto a substrate, and crystallizing it to said layer, characterized in that the precursor solution according to claim 6 is used.

8. A method according to claim 7, characterized in that:
- the substrate surface onto which the precursor solution is applied, is provided with a first electrode;
  - the said layer is structured according to a desired pattern and
  - on top of the said layer a second electrode is provided.

9. A method as claimed in claim 7, wherein the substrate is a semiconductor substrate in which a first active component is defined.

10. A method as claimed in claim 9, wherein the active component, the capacitor and at least one resistor are mutually interconnected so as to provide a combined ESD-protection and decoupling function.

11. An electronic device comprising a crystalline layer of an oxide of lead, niobium and a third metal on a substrate obtainable by the method of any of the claims 7-10.